



General Description

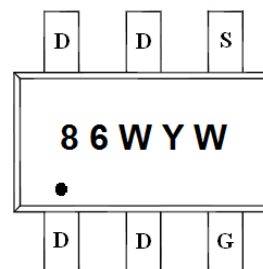
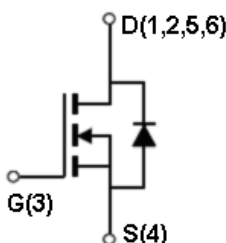
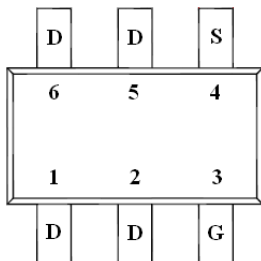
AFN3486W, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- $I_D=3.0A, R_{DS(ON)}=315m\Omega@V_{GS}=10V$
- $I_D=2.0A, R_{DS(ON)}=295m\Omega@V_{GS}=10V$
- $I_D=2.0A, R_{DS(ON)}=300m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23-6L package design

Pin Description (SOT-23-6L)



Application

- DC/DC Converters
- Load Switch
- LED Backlighting in LCD TVs

Pin Define

Pin	Symbol	Description
1	D	Drain
2	D	Drain
3	G	Gate
4	S	Source
5	D	Drain
6	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN3486WS26RG	86WYW	SOT-23-6L	Tape & Reel	3000 EA

※ 86W parts code

※ Y year code (0 ~ 9)

※ W week code (A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52)

※ AFN3486WS26RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	105	V
Gate –Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	T _c =25°C	3.0
		T _c =70°C	2.0
Pulsed Drain Current	I _{DM}	10	A
Continuous Source Current(Diode Conduction)	I _S	1.6	A
Power Dissipation		T _A =25°C	2.0
		T _A =70°C	1.3
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	120	°C/W

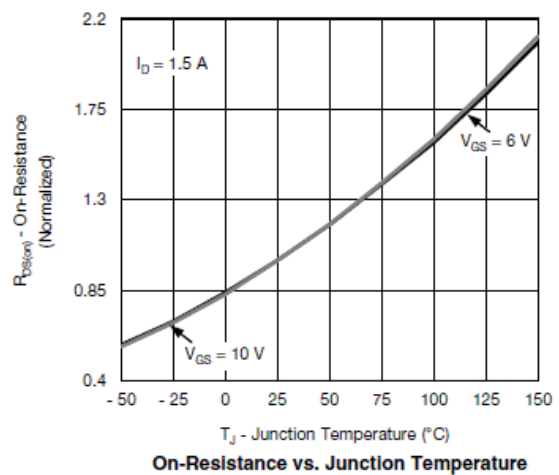
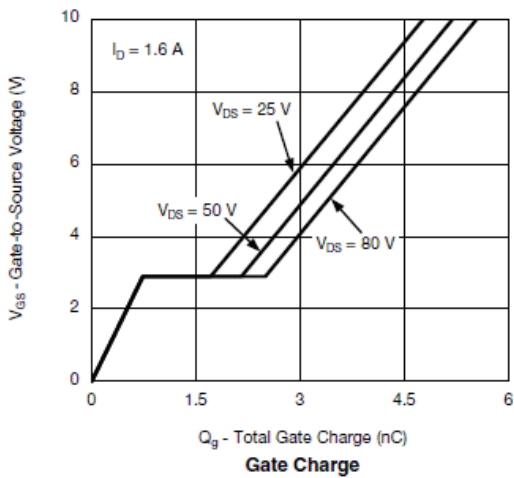
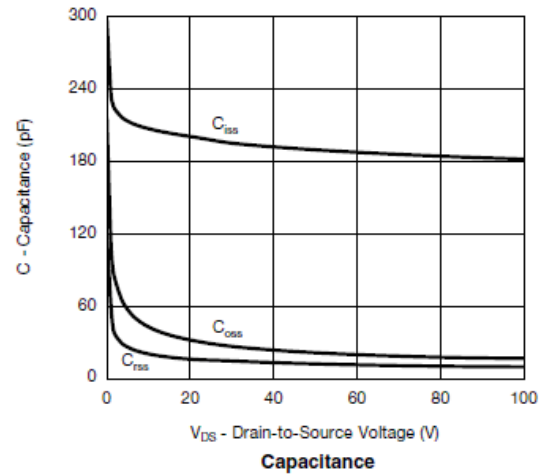
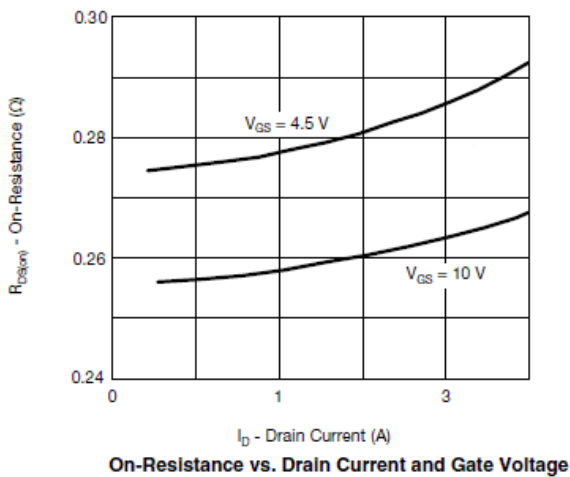
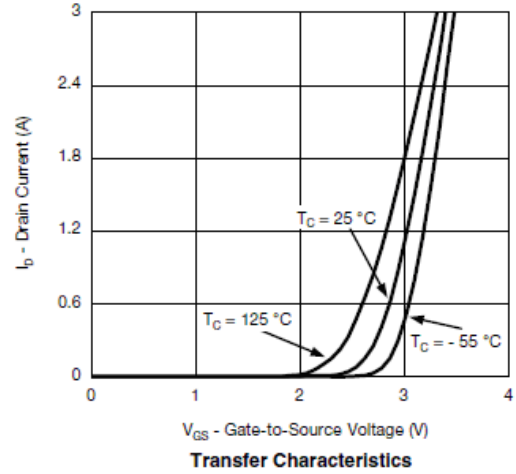
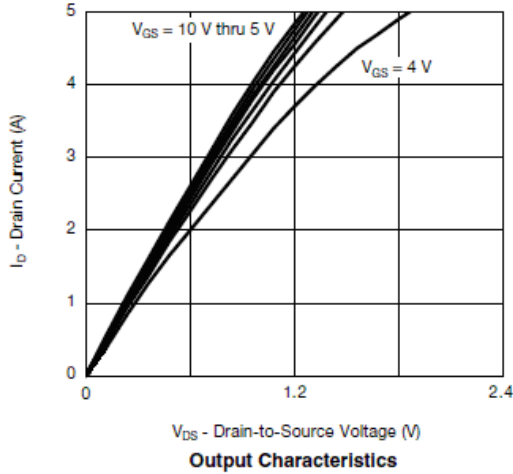
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	105	108		V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.0		2.5	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V			1	uA
		V _{DS} =80V, V _{GS} =0V T _J =85°C			10	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 5V, V _{GS} =4.5V	10			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =3.0A		295	315	mΩ
		V _{GS} =10V, I _D =2.0A		270	295	
		V _{GS} =4.5V, I _D =2.0A		282	300	
Forward Transconductance	g _{FS}	V _{DS} =20V, I _D =1.5A		2		S
Diode Forward Voltage	V _{SD}	I _S =1.3A, V _{GS} =0V		0.85	1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =50V, V _{GS} =4.5V I _D ≧1.6A		2.8	5.8	nC
Gate-Source Charge	Q _{gs}			0.75		
Gate-Drain Charge	Q _{gd}			1.4		
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V f=1MHz		200		pF
Output Capacitance	C _{oss}			22		
Reverse Transfer Capacitance	C _{rss}			13		
Turn-On Time	t _{d(on)}	V _{DD} =50V, R _L =39Ω I _D ≧1.3A, V _{GEN} =4.5V R _G =1Ω		25	50	ns
	t _r			20	50	
Turn-Off Time	t _{d(off)}			15	30	
	t _f			10	25	

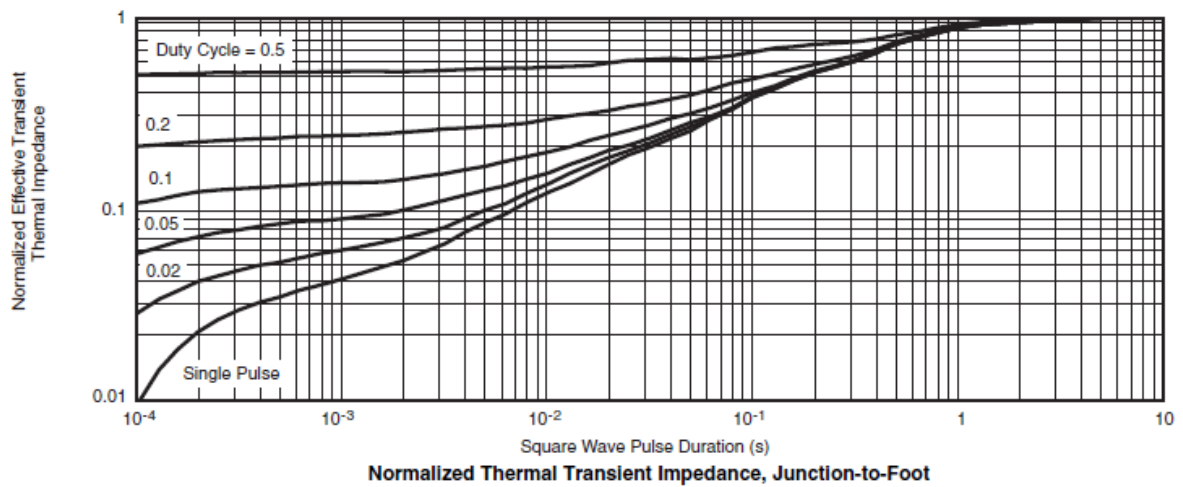
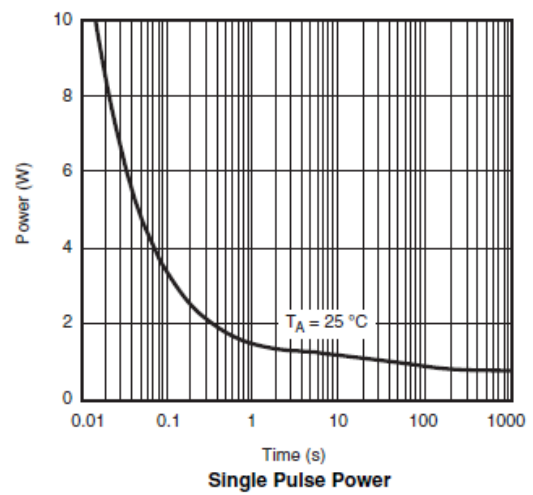
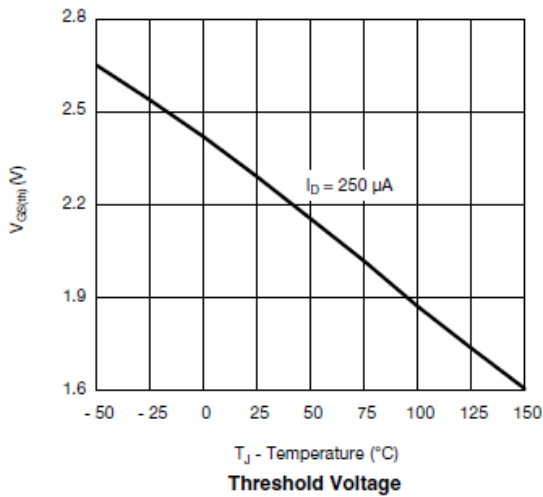
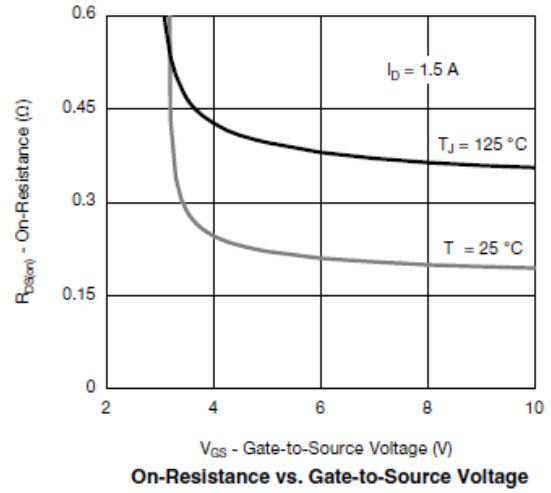
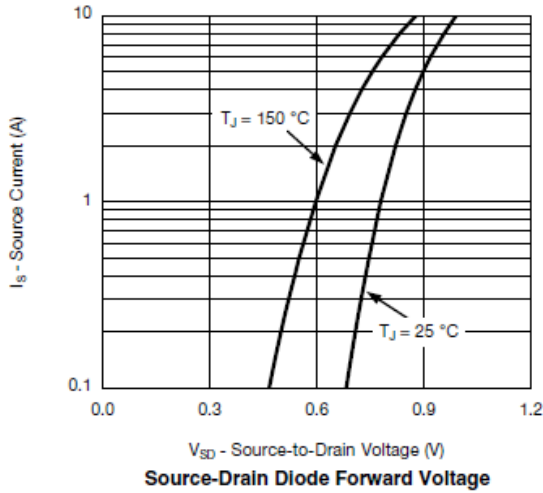


Typical Characteristics





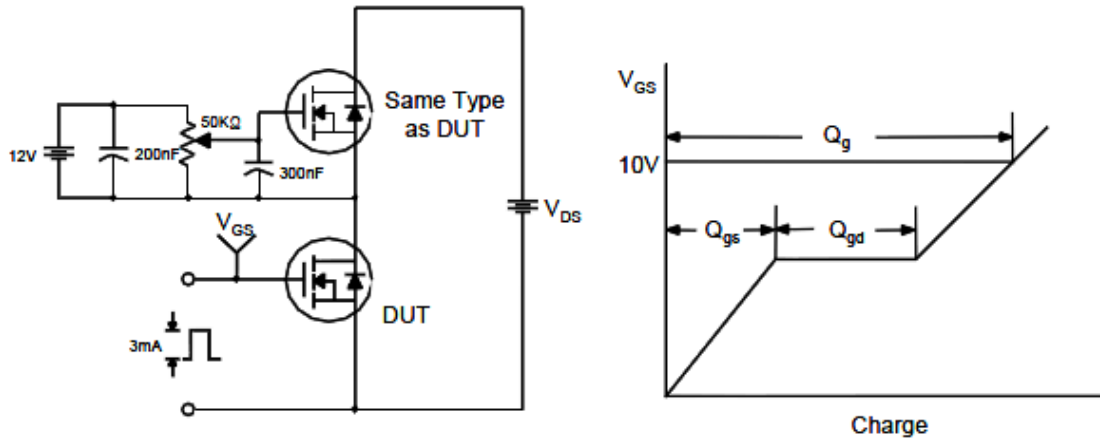
Typical Characteristics



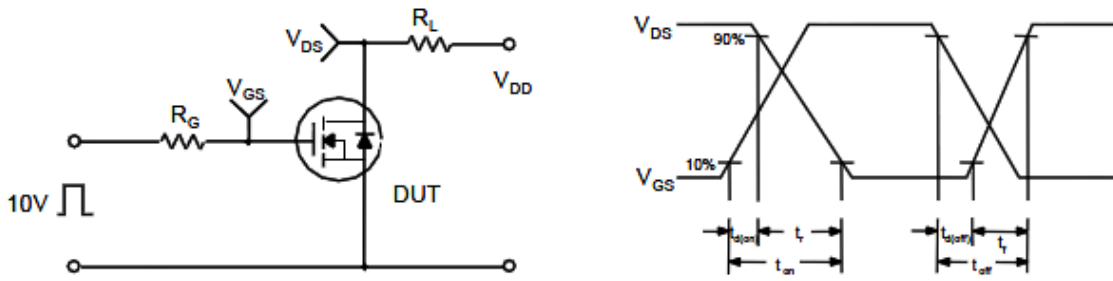


Typical Characteristics

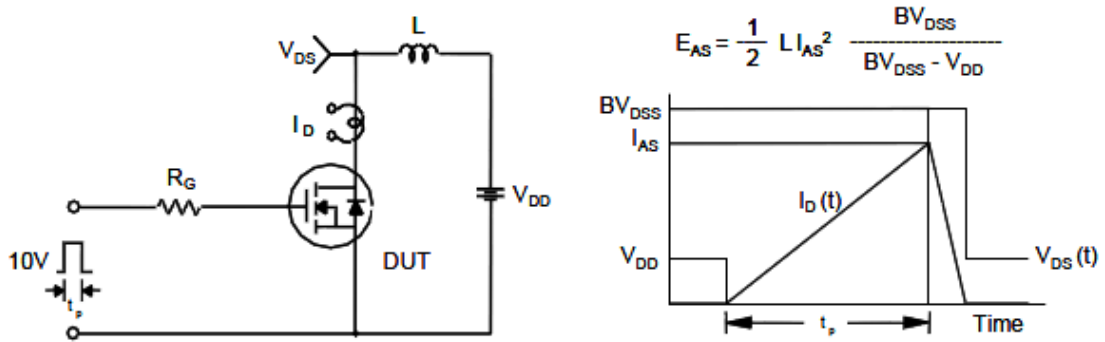
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

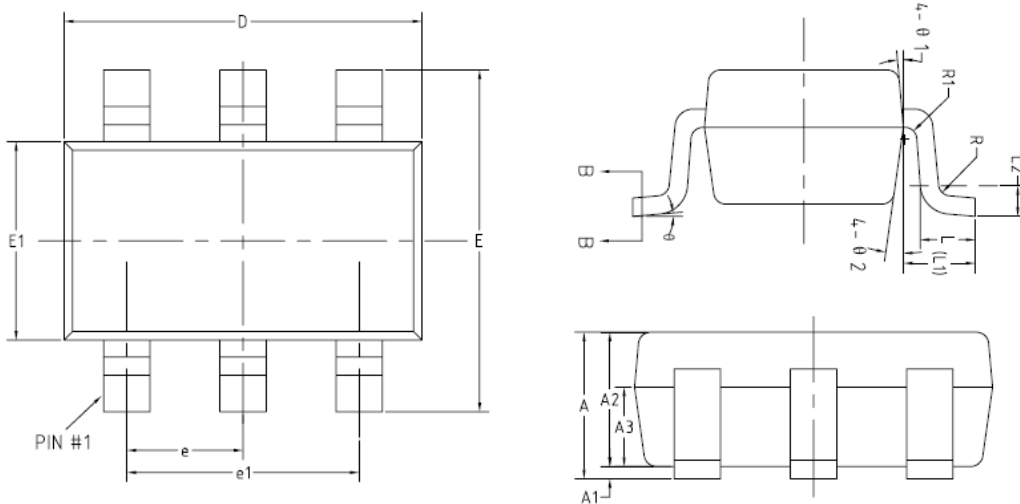


Unclamped Inductive Switching Test Circuit & Waveforms





Package Information (SOT-23-6L)



(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	—	—	1.45
A1	0	—	0.15
A2	0.90	1.10	1.30
A3	0.60	0.65	0.70
b	0.39	—	0.49
b1	0.38	0.40	0.45
c	0.12	—	0.19
c1	0.11	0.13	0.15
D	2.85	2.95	3.05
E	2.60	2.80	3.00
E1	1.55	1.65	1.75
e	0.85	0.95	1.05
e1	1.80	1.90	2.00
L	0.35	0.45	0.60
L1	0.59REF		
L2	0.25BSC		
R	0.05	—	—
R1	0.05	—	0.20
θ	0°	—	8°
θ 1	8°	10°	12°
θ 2	8°	10°	12°

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